

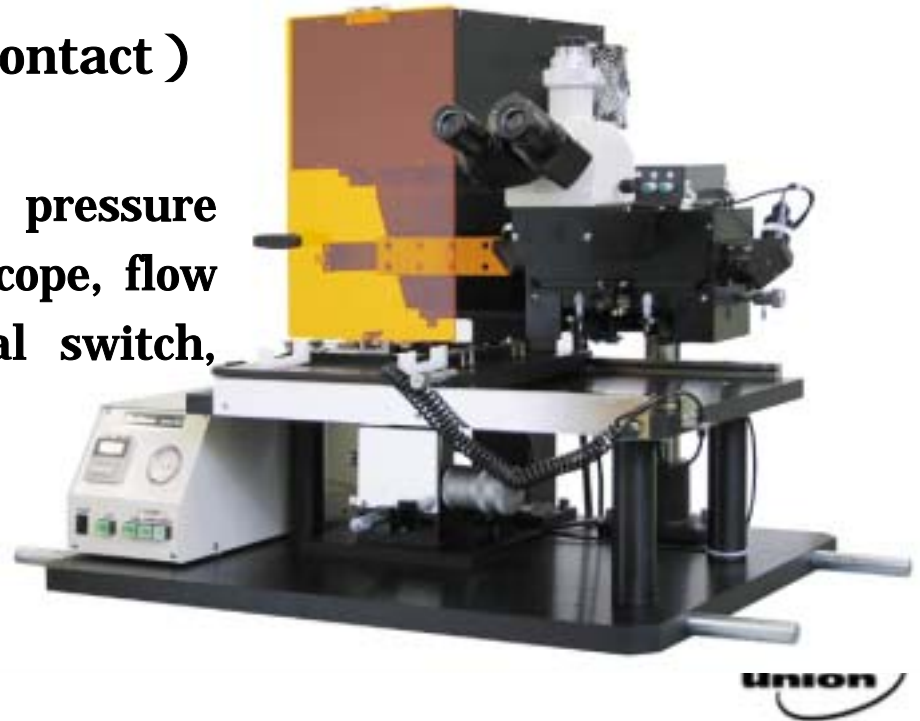
# **EMA-400**

Desk Top Mask Aligner



- **Mask size; 5-inch max.**
- **Wafer size; 4-inch max.**
- **Integrator lens for exposure**
- **Soft contact method**
- **Hard contract method (option)**
- **Resolution; 3  $\mu$  m L/S at soft contact  
2  $\mu$  m L/S at hard contact )**

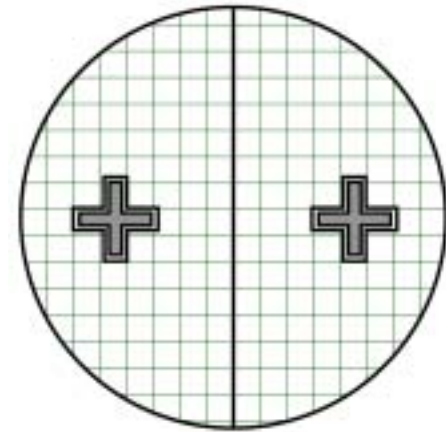
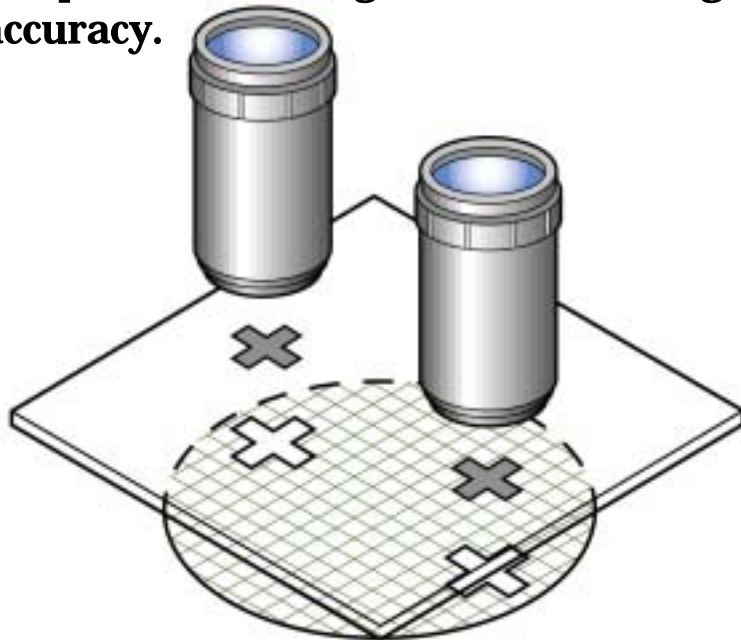
**Application: Ink-jet printer head, pressure sensor, acceleration sensor, gyroscope, flow path module, HDD head, optical switch, DNA analysis chip, active catheter**



## ● Easy alignment with Split-Field Microscope (split-field image alignment scope)

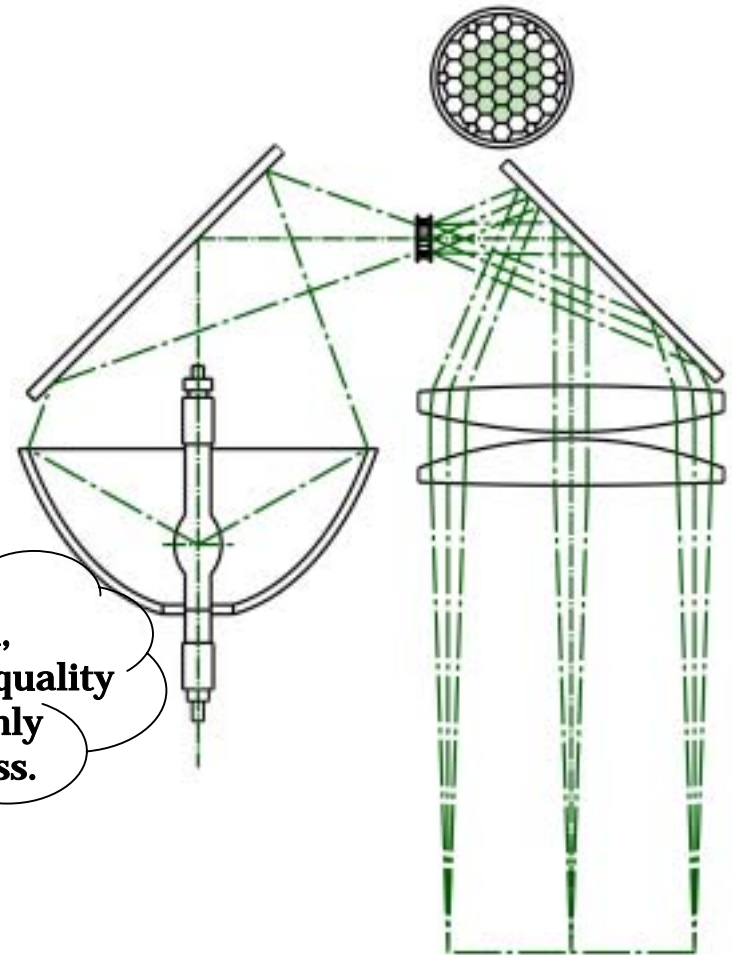
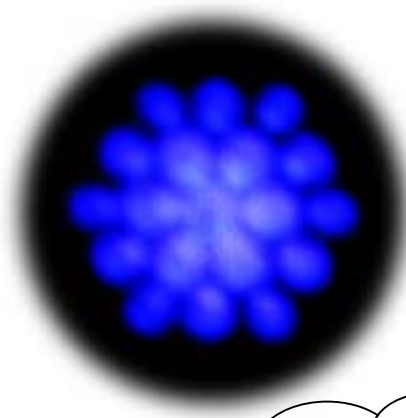
Microscope is used to make an alignment (position adjustment) between mask & wafer

Confirming alignment marks in the double visual field can avoid discrepancy between mask & wafer, and it competes with large size mask aligner in alignment accuracy.



- 1) Low-end machine, but having Split-Field Microscope
  - \*Making alignment accuracy improved
  - \*Alignment accuracy is less than  $\pm 3 \mu m$
- 2) Objective lens separation 15 to 75mm variable to meet small amorphous size of wafer

## ● Integrated lens for exposure



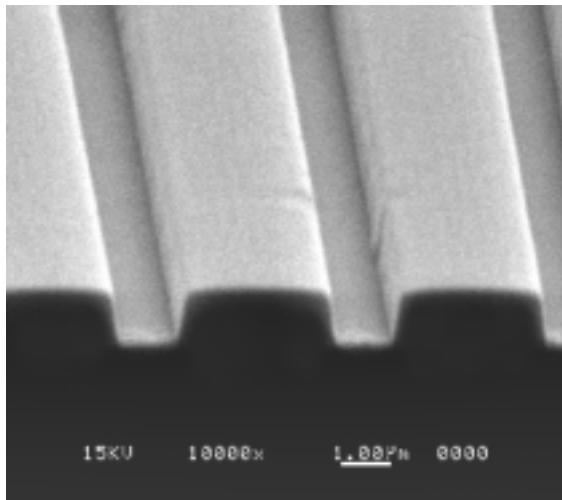
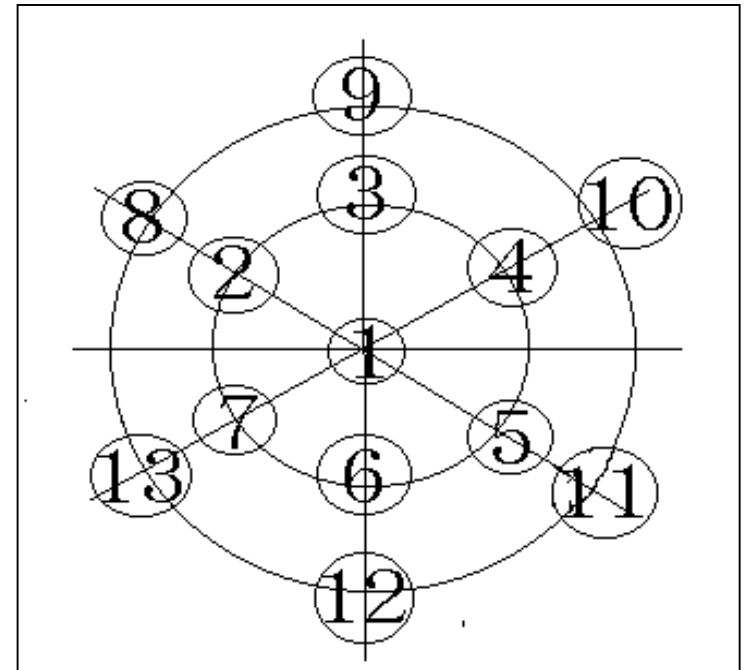
**This is differential,  
competitive, high-quality  
lens to expose evenly  
without unevenness.**

- 1) Light beam directions are parallel
- 2) Parallel angle is within 1 degree
- 3) The more all the light beams run parallel onto mask, the more illumination system becomes effective for exposure
- 4) Lens surface looks like honeycomb structure

## ● Unevenness in illumination intensity of integrated lens

measuring points mentioned right, then  
figuring out illumination intensity =  $(MAX-MIN)/(MAX+MIN)$  within  $\pm 5\%$

Even exposure in an area of 4-inch can be  
achieved

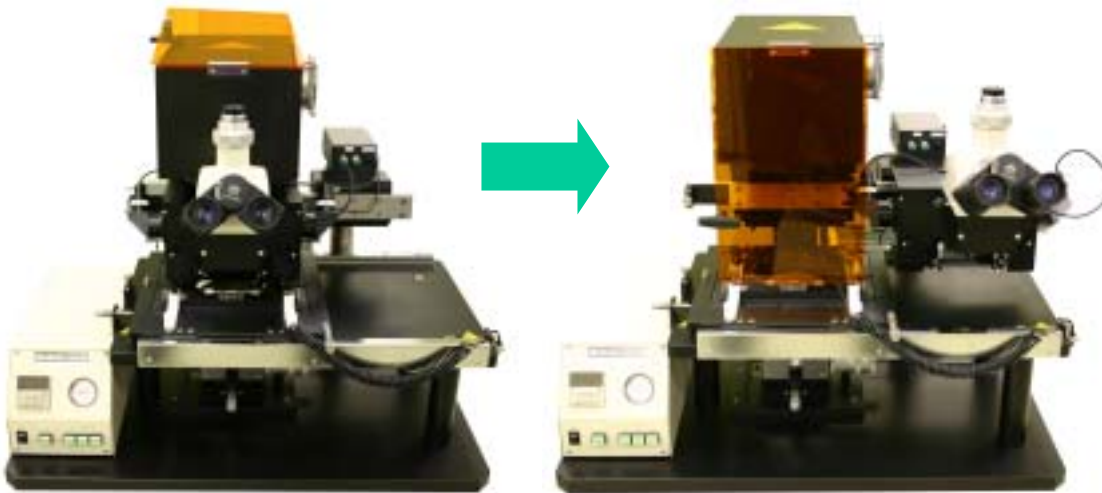


## ● Red LED 630nm is adopted as an illumination for alignment

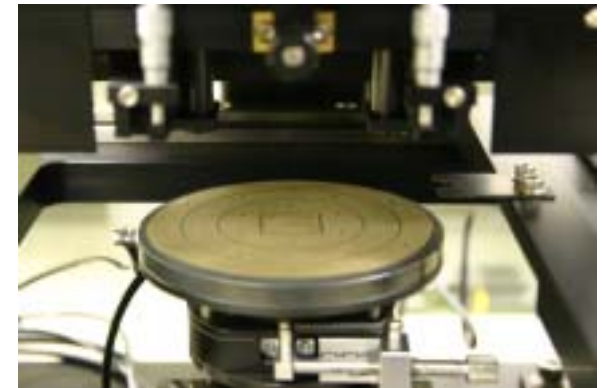
Advantages of adopting LED as compared with normal  
lighting;

- \* No exposure is done during alignment, because of monochromatic light (red).
- \* Life span is longer than normal lighting; accordingly frequency of light source exchange is less.

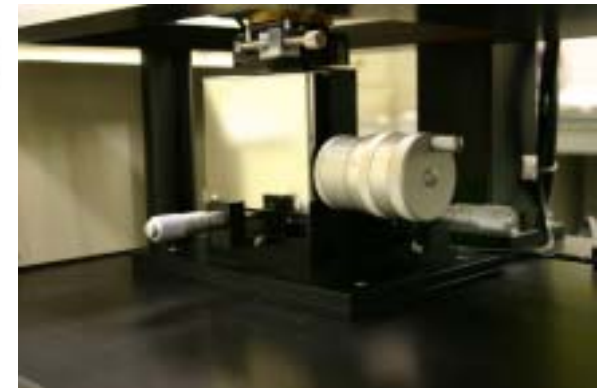
- Pursuing better operability with mask sliding method and 4-axis (X,Y,theta & Z) wafer stage unit
- Multi-wafer chuck is adopted to meet from small amorphous size of wafer to 4-inch wafer



- 1) Sliding a stage unit and optical tube unit to right side, then put a specimen onto wafer chuck
- 2) Sliding the optical unit back to confirm alignment, then put down a cover to expose



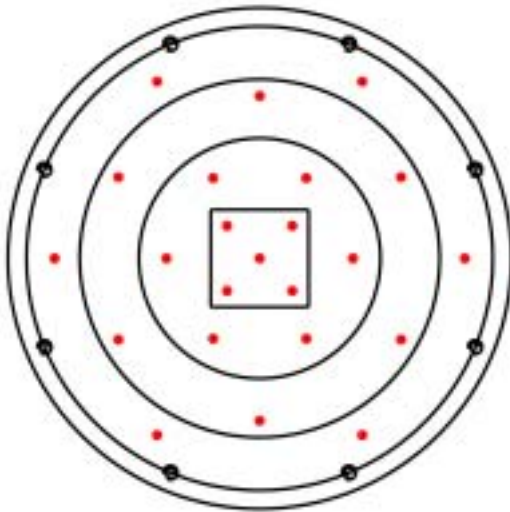
Multi-wafer chuck  
(Stage to put a wafer on)



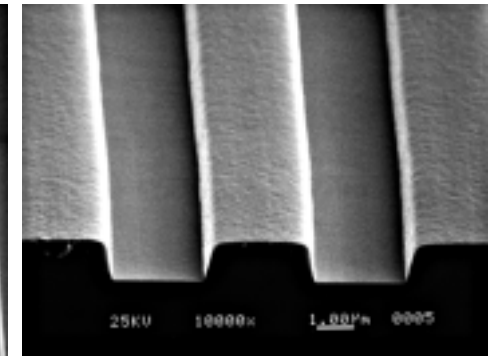
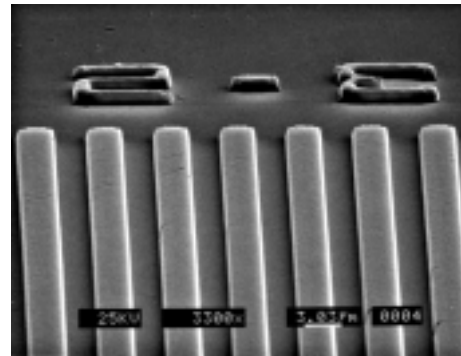
Micrometers are adopted for stage to be moved it from side to side and up and down.

- **Resolution less than  $2\ \mu\text{m}$  L/S can be realized with an optional function: hard contact method (N<sub>2</sub> blowing up)**

**N<sub>2</sub> Blowing Up Method: Blowing up a wafer by N<sub>2</sub> (or dry air) from beneath to contact it to a mask (hard contact)**

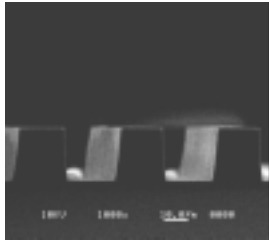


**Blowing up or absorbing by N<sub>2</sub> from holes on multi-wafer chuck**

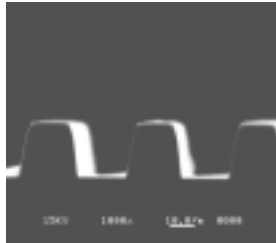


**Hand contact method can realize clear edge on exposure**

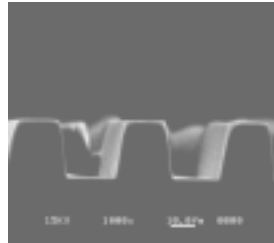




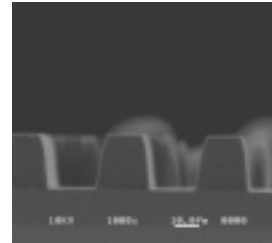
**Hard contact**



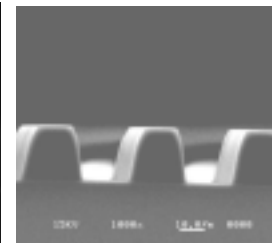
**Gap 0  $\mu$  m**



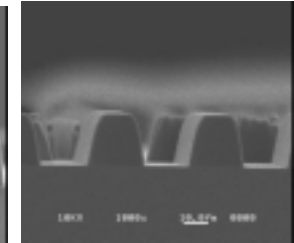
**Gap 10  $\mu$  m**



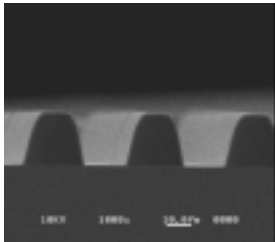
**Gap 20  $\mu$  m**



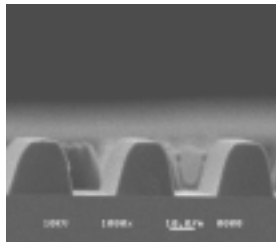
**Gap 30  $\mu$  m**



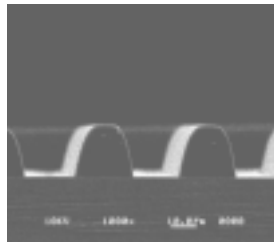
**Gap 40  $\mu$  m**



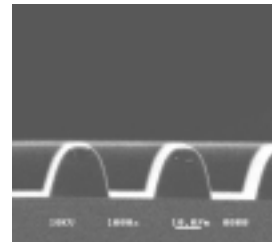
**Gap 50  $\mu$  m**



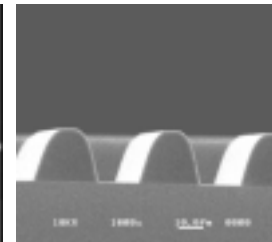
**Gap 60  $\mu$  m**



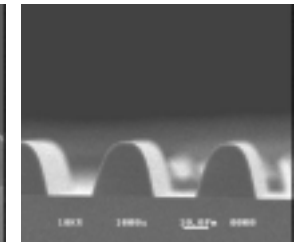
**Gap 70  $\mu$  m**



**Gap 80  $\mu$  m**

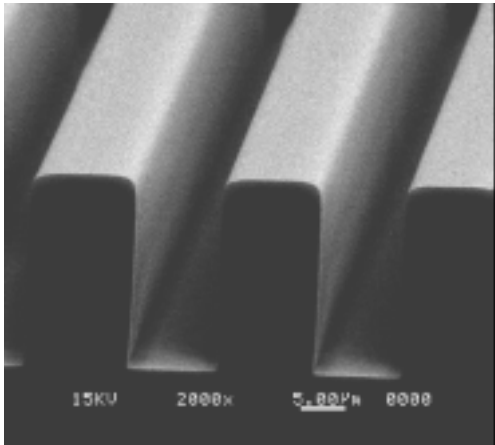


**Gap 90  $\mu$  m**

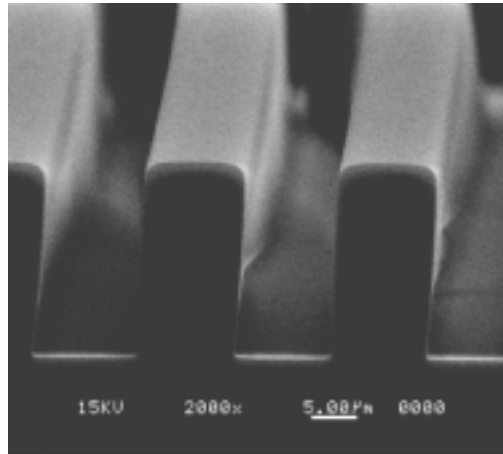


**Gap 100  $\mu$  m**

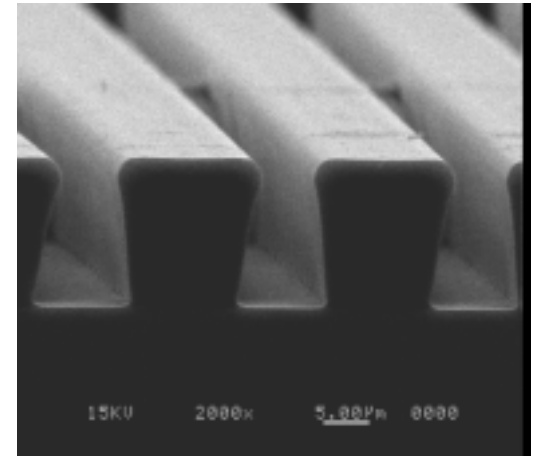




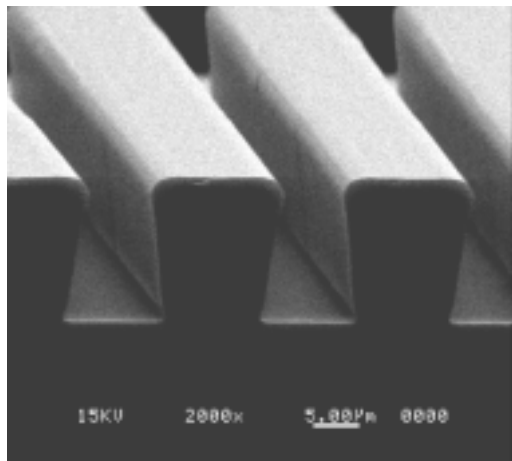
**PMER / Gap 0 μ m**



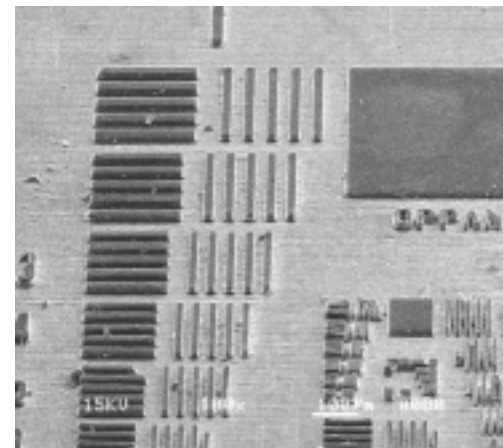
**PMER / Gap 20 μ m**



**SU8 / Gap 0 μ m**



**SU8 / Gap 20 μ m**



**using Toppan Chart**